

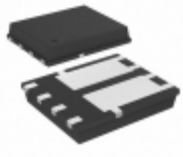

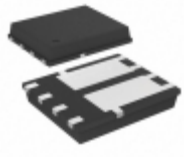
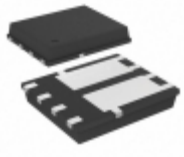
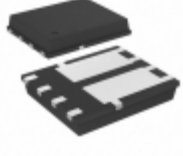
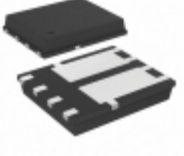
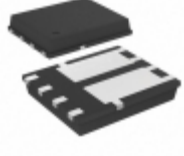
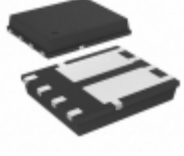
	<h2 style="color: #E67E22;">SI7980DP-T1-GE3</h2>
 <p>Image may be representation. See specs for product details.</p>	Hersteller-Teilenummer: SI7980DP-T1-GE3
	Hersteller / Marke: Electro-Films (EFI) / Vishay
	Teil der Beschreibung: MOSFET 2N-CH 20V 8A PPAK SO-8
	Datenblätter:  SI7980DP-T1-GE3.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 800915 pcs Stock Available.
	Liefern von: Hong Kong
Versandweg: DHL/Fedex/TNT/UPS/EMS	

Spezifikationen

Teilenummer	SI7980DP-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2N-CH 20V 8A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	800915 pcs Stock
detaillierte Beschreibung	Mosfet Array 2 N-Channel (Half Bridge) 20V 8A 19.8W,
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	19.8W, 21.9W
Verpackung / Gehäuse	PowerPAK® SO-8 Dual
Supplier Device-Gehäuse	PowerPAK® SO-8 Dual
Typ FET	2 N-Channel (Half Bridge)
FET-Merkmal	Standard
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A
Rds On (Max) @ Id, Vgs	22 mOhm @ 5A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	27nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1010pF @ 10V
Verpackung	Tape & Reel (TR)
Basisteilenummer	SI7980
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7980DP-T1-GE3TR







SI7980DP-T1-GE3 ist neu im Original, Suche SI7980DP-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7980DP-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7980DP-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7980DP-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 20V 8A PPAK SO-8</p>	 <p>SI7980DP SI SI7980DP SI</p>	 <p>SI7980DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 8A PPAK SO-8</p>	 <p>SI7980DP-T1-E3 Vishay / Siliconix MOSFET 2N-CH 20V 8A PPAK SO-8</p>
 <p>SI7983DP-T1-E3 Vishay / Siliconix MOSFET 2P-CH 20V 7.7A PPAK SO-8</p>	 <p>SI7983DP-T1-GE3 Vishay / Siliconix MOSFET 2P-CH 20V 7.7A PPAK SO-8</p>	 <p>SI7972DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2 N-CH 30V POWERPAK SO8</p>	 <p>SI7983DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 7.7A PPAK SO-8</p>

heiße Teile

Mehr

 SI7922DN-T1-GE3	 SI7922DN-T1-GE3	 SI7923DN-T1-E3	 SI7923DN-T1-E3	 SI7923DN-T1-GE3
 SI7923DN-T1-GE3	 SI7938DP-T1-GE3	 SI7938DP-T1-GE3	 SI7940DP	 SI7940DP-T1-E3
 SI7940DP-T1-E3	 SI7941DP-T1-E3	 SI7941DP-T1-GE3	 SI7942DP	 SI7942DP-T1-E3
 SI7942DP-T1-E3	 SI7942DP-T1-GE3	 SI7942DP-T1-GE3	 SI7945DP-T1-E3	 SI7945DP-T1-E3
 SI7946DP	 SI7946DP-T1-E3	 SI7946DP-T1-E3	 SI7948DP	 SI7948DP-T1-E3
 SI7949DP-T1-GE3	 SI7949DP-T1-GE3	 SI7956DP-T1-GE3	 SI7956DP-T1-GE3	 SI7958DP
 SI7958DP-T1-E3	 SI7958DP-T1-E3	 SI7958DP-T1-GE3	 SI7958DP-T1-GE3	 SI7960DP-T1-E3
 SI7960DP-T1-E3	 SI7960DP-T1-GE3	 SI7960DP-T1-GE3	 SI7964DP	 SI7964DP-T1-GE3
 SI7964DP-T1-GE3	 SI7970DP	 SI7970DP-T1-E3	 SI7980DP-T1-E3	 SI7980DP-T1-E3
 SI7980DP-T1-GE3	 SI7997DP-T1-GE3	 SI7997DP-T1-GE3	 SI7998DP-T1-GE3	 SI7998DP-T1-GE3

Contact us: Info@Y-IC.com

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